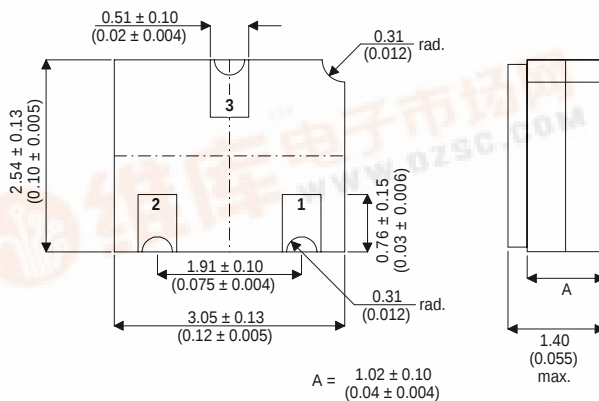


1N4149CSM

MECHANICAL DATA

Dimensions in mm (inches)

**SOT23 CERAMIC
(LCC1 PACKAGE)****Underside View**

PAD 1 — Anode PAD 2 — Not Connected PAD 3 — Cathode

**SILICON EPITAXIAL
PLANAR DIODE**

General Purpose and
Switching Diode in
Hermetic Ceramic Surface Mount
Package for
High Reliability Applications

ABSOLUTE MAXIMUM RATINGS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_R	Reverse Voltage			100	V
V_{RRM}	Repetitive Peak Reverse Voltage			100	V
$I_{F(AV)}$	Average Rectified Forward Current			150	mA
I_F	Forward Current			200	mA
I_{FRM}	Repetitive Peak Forward Current			450	mA
I_{FSM}	Non-Repetitive Peak Forward Current	$t = 1\mu\text{s}$ $t = 1\text{s}$		2000	mA
				500	
P_{tot}	Power Dissipation at $T_{\text{amb}} = 25^{\circ}\text{C}$			500	mW

CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage			1	V
I_R	Reverse Current			25	nA
	$V_R = 20\text{V}$, $T_j = 150^{\circ}\text{C}$			50	μA
$V_{(BR)R}$	Reverse Avalanche Breakdown Voltage	$I_R = 100\mu\text{A}$	100		V
		$I_R = 5\mu\text{A}$	100		V
C_d	Capacitance			4	pF
V_r	Forward Recovery Voltage			2.5	V
t_{rr}	Reverse Recovery Time			4	ns